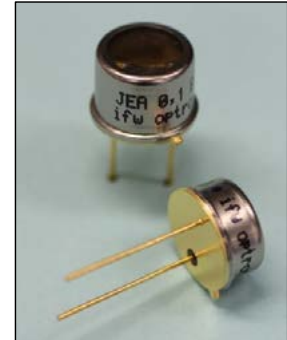


SiC-Photodiode with integrated UV-filter
JEA0,1A · JEA0,1B · JEA0,1C

Characteristics :

- ◆ small area SiC-photodiode
- ◆ active area: 0,1 mm²
- ◆ UV-filters for UVA-, UVB- and UVC-range
- ◆ more filter options on request
- ◆ hermetically sealed TO-package
- ◆ RoHS, REACH and WEEE conform



Applications :

- ◆ optical measurement in UV-range with selected spectral range
- ◆ control of sterilization lamps
- ◆ flame control
- ◆ sun light measurement

Maximum Ratings :

- ◆ reverse voltage 10 V
- ◆ operating temperature range - 40 °C ... 125 °C
- ◆ storage temperature range - 40 °C ... 125 °C
- ◆ soldering temperature (3s) 260 °C

Versions:

| Filter | Anode: isolated Cathode: case-pin | Cathode: isolated Anode: case-pin | Anode, Cathode: isolated Additional case-pin | Operating Temperature: 150 °C |
|--------|--------------------------------------|--------------------------------------|---|-------------------------------|
| UV-A | JEA0,1A | JEAC0,1A | JEA0,1A-I | *-HT |
| UV-B | JEA0,1B | JEAC0,1B | JEA0,1B-I | |
| UV-C | JEA0,1C | JEAC0,1C | JEA0,1C-I | |

Further available optical filters:

| Filter | Spectral-range | Part |
|----------|----------------|-------------|
| UV-AB | 280-395 nm | JEA0,1AB |
| UV-BC | 228-322 nm | JEA0,1BC |
| UV-DVGW | 240-290 nm | JEA0,1DVGW |
| UV-A-350 | 300-400 nm | JEA0,1A-350 |
| UV-A-365 | 350-400 nm | JEA0,1A-365 |
| Erythema | CIE 87 | JEA0,1E |

Further available active areas:

| Active Area |
|----------------------|
| 0,05 mm ² |
| 0,25 mm ² |
| 1 mm ² |
| 2 mm ² |
| 5 mm ² |

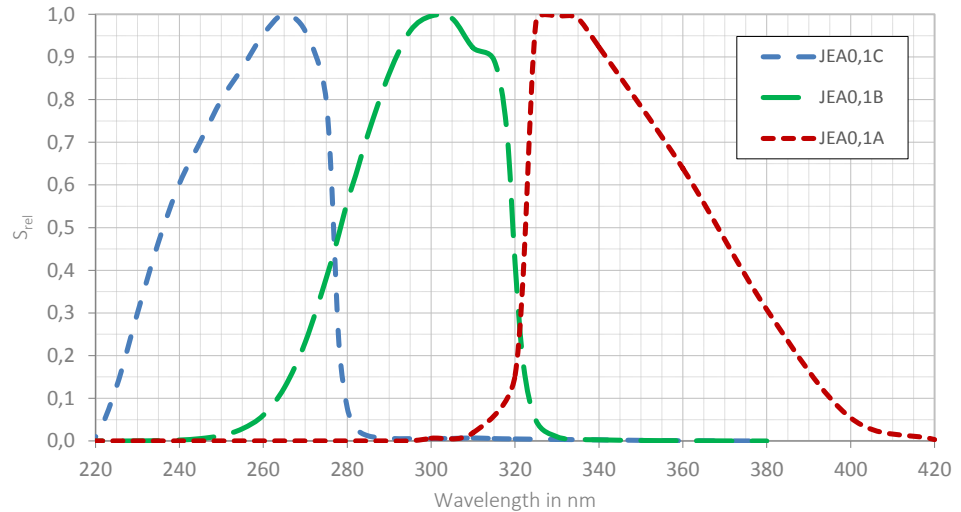
Further available packages:

| Package | Parts | Datasheet |
|---------|---------------|------------|
| TO18 | JEA0,1A/B/C-S | on request |

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SiC-Photodiode with integrated UV-filter JEA0,1A · JEA0,1B · JEA0,1C

Relative Spectral Responsivity S_{rel} :



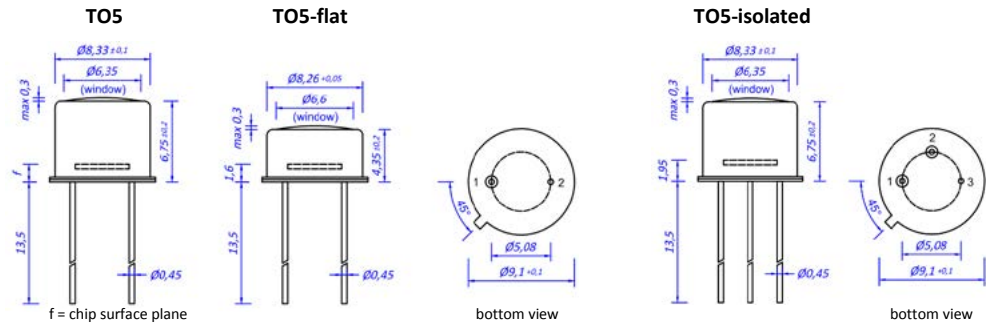
Technical Data:

| Parameter | Test Conditions | UV-A | UV-B | UV-C | Einheit |
|------------------------------------|------------------|---------------|------|----------|-----------------|
| active area | | 0,365 x 0,365 | | | mm ² |
| spectral range | λ_{min} | 318 | 265 | 225 | nm |
| | λ_{max} | 395 | 322 | 280 | nm |
| wavelength of maximum responsivity | λ_{Smax} | 330 | 300 | 265 | nm |
| maximum responsivity S_{max} | $S = S_{max}$ | 0,14 | 0,14 | 0,18 | A/W |
| dark current I_R | $U_R = 1 V$ | 10 | | | fA |
| junction capacitance C_j (max.) | $f = 10 kHz$ | 13 (20) | | | pF |
| field of view | Anode isolated | ±30 | ±30 | ±45 | degree |
| | Cathode isolated | ±27 | | | |
| | A. + C. isolated | ±28 | | | |
| weight | | 1,1 | | | gram |
| package/drawing | Anode isolated | TO5 | TO5 | TO5-flat | |
| | Cathode isolated | TO5 | | | |
| | A. + C. isolated | TO5-isolated | | | |

typical values; test conditions, as not otherwise specified: $T_A = 25 ^\circ C$, $U_R = 0 V$

SiC-Photodiode with integrated UV-filter JEA0,1A · JEA0,1B · JEA0,1C

Package Dimensions:

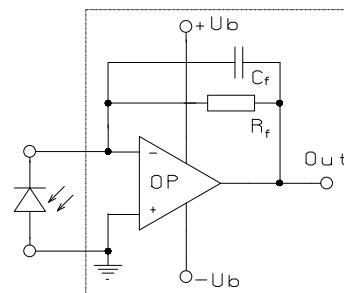


Anode isolated: Pin 1: Anode
Pin 2: Cathode + Case
f = 1,6 mm

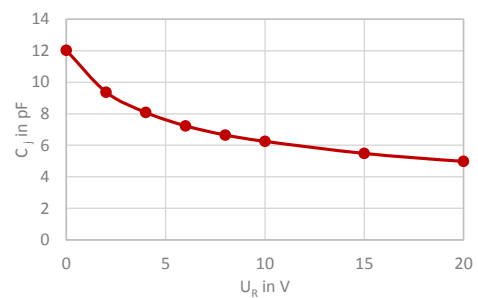
Anode + Cathode isolated: Pin 1: Anode
Pin 2: Cathode
Pin 3: Case

Cathode isolated: Pin 1: Cathode
Pin 2: Anode + Case
f = 1,85 mm

Application Example:



Junction Capacitance C_j vs. Reverse Voltage U_R :



The application example shows a typical circuit R_f is responsible for the gain of the circuit C_f compensates the reverse junction capacitance of the photodiode and the input capacitance of the opamp. The exact value of C_f depends on R_f , used opamp and capacitance of the circuit. A typical value is 1pF.

The chart shows the typical dependence of junction capacitance C_j vs. applied reverse voltage U_R . Lower intrinsic capacitance can be used to increase the bandwidth (lower the rise time) in electric circuits.